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In re application of: Nakamura et al. ATTORNEY DOCKET NO: P97,0322  
Serial No.: 08/809,463 GROUP ART UNIT: 2814  
Filed: July 18, 1997 EXAMINER: N. Kelley  
For: "MULTI-LAYERED STRUCTURE FOR FABRICATING AN OHMIC ELECTRODE AND OHMIC ELECTRODE"

**AMENDMENT**

RECEIVED

JUN 15 1998

GROUP 2100

Assistant Commissioner for Patents  
Washington D.C. 20231

SIR:

Transmitted herewith is an amendment in the above-identified application.

■ No additional fee is required.

The fee has been calculated as shown below.

CLAIMS AS AMENDED						
	(2) CLAIMS REMAINING AFTER AMENDMENT		(4) HIGHEST NO. PREVIOUSLY PAID FOR	(5) PRESENT EXTRA	(6) RATE	(7) ADDITIONAL FEE
TOTAL CLAIMS	*	MINUS	**	X	( ) X 11.00 ( ) X 22.00	\$
INDEP. CLAIMS	*	MINUS		X	( ) X 40.00 ( ) X 80.00	\$
Application amended to contain any multiple dependent claims not previously paid for.				( ) YES ( ) NO	( ) \$130.00 ( ) \$260.00 ONE TIME	
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT						\$

\* If the entry in Column 2 is less than the entry in Column 4, write "0" in Column 5.

\*\* If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20 write "20" in this space.

- ☐ Applicant petitions the Commissioner of Patents and Trademarks to extend this time for response is for \_\_\_ months so that the period for response is extended to \_\_\_. A \_\_\_ check is attached to cover the cost of the extension. Any deficiency or overpayment should be charged or credited to deposit account No. 08-2290. A duplicate copy of this sheet is enclosed.
- ☐ A check in the amount of \$ \_\_\_ is attached to cover the extension fee.
- ☐ A check for \$ \_\_\_ accompanying IDS under 37 CFR 1.97(c) is attached
- ☐ A check for \$ \_\_\_ and Petition for Consideration of IDS under 37 CFR 1.97(d) is attached.
- ☒ The Commissioner is hereby authorized to charge any additional fees which may be required, or to credit any overpayment to account No. 08-2290. A duplicate of this sheet is enclosed.
- When phoning re this application, please call 312/876-0200, ext. 3191.

HILL & SIMPSON

A Professional Corporation

BY Robert J. Depke (Reg. No. 37,607)

ROBERT J. DEPKE

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231 on June 5, 1998.

ROBERT J. DEPKE (Reg. No. 37,607)

NAME OF APPLICANT'S ATTORNEY

SIGNATURE

June 5, 1998

DATE



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

AMENDMENT "A"

APPLICANTS: Nakamura et al. ATTORNEY DOCKET NO: P97,0322  
SERIAL NO: 08/809,463 GROUP ART UNIT: 2814  
FILED: July 18, 1997 EXAMINER: N. Kelley  
TITLE: "MULTI-LAYERED STRUCTURE FOR FABRICATING AN OHMIC  
ELECTRODE AND OHMIC ELECTRODE"

Assistant Commissioner for Patents  
Washington, D.C. 20231  
S I R:

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JUN 15 1998

GROUP 2814

In response to the Office Action dated March 5, 1998, Applicants herewith amend the application as follows:

IN THE CLAIMS

A1  
B1  
1. A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body.

A2  
4. The multi-layered structure for fabricating an ohmic electrode according to claim 1 wherein said film comprises a metal film and [a] wherein the metal nitride film [provided] is formed on said metal film.

A3  
6. The multi-layered structure for fabricating an ohmic electrode according to claim 5 wherein a further metal film for wiring is further provided on said refractory metal film.

A4  
B2  
9. A multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body,